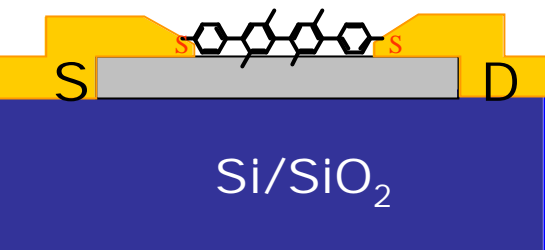
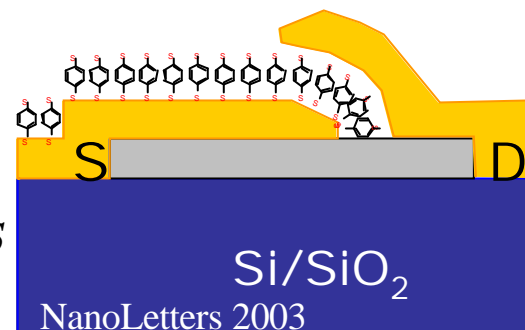


# Electrical measurements on phenylene-based conjugated molecules



**Günther Lientschnig**

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**Jeong-O Lee, Frank Wiertz, Peter Hadley, Cees Dekker**

*Department of NanoScience and DIMES, TU Delft*

**Richard Egberingk, David Reinhoudt**

*University of Twente*

**Martin Struijk, René Janssen**

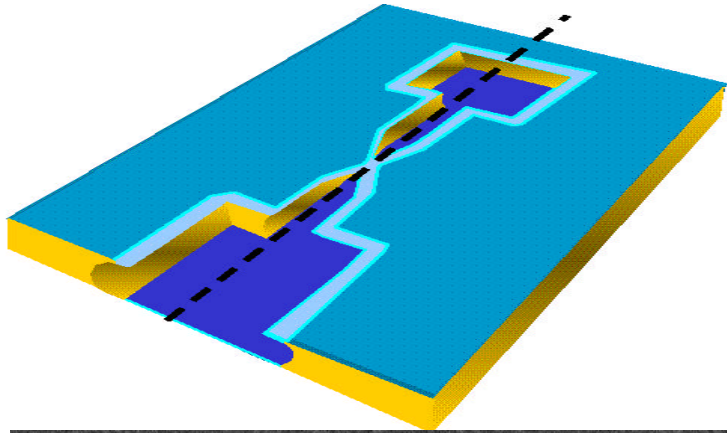
*TU Eindhoven*

**Andrew Grimsdale**

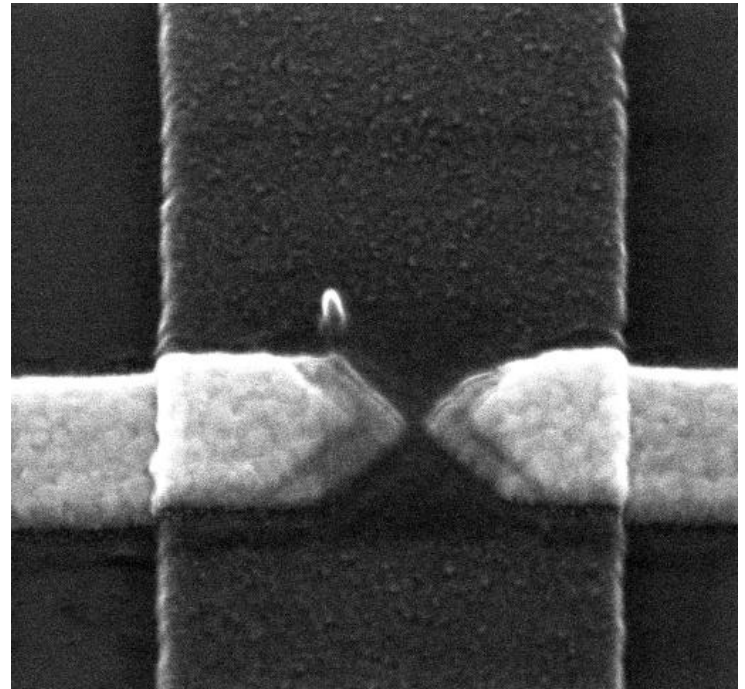
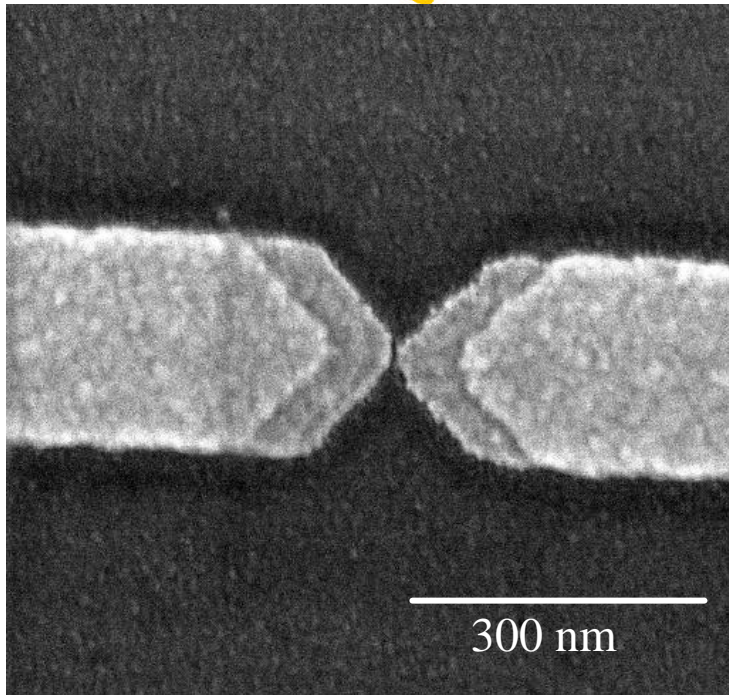
*MPIP Mainz*



# Long Molecules: Device Fabrication

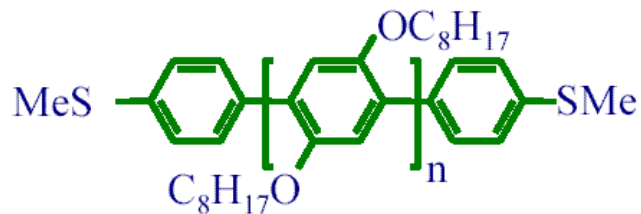
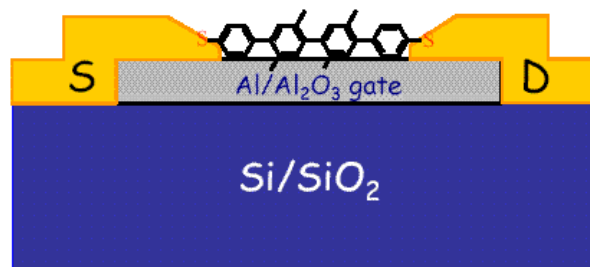


- Al Gate
- Double layer resist
- Shadow evaporation
- Liftoff

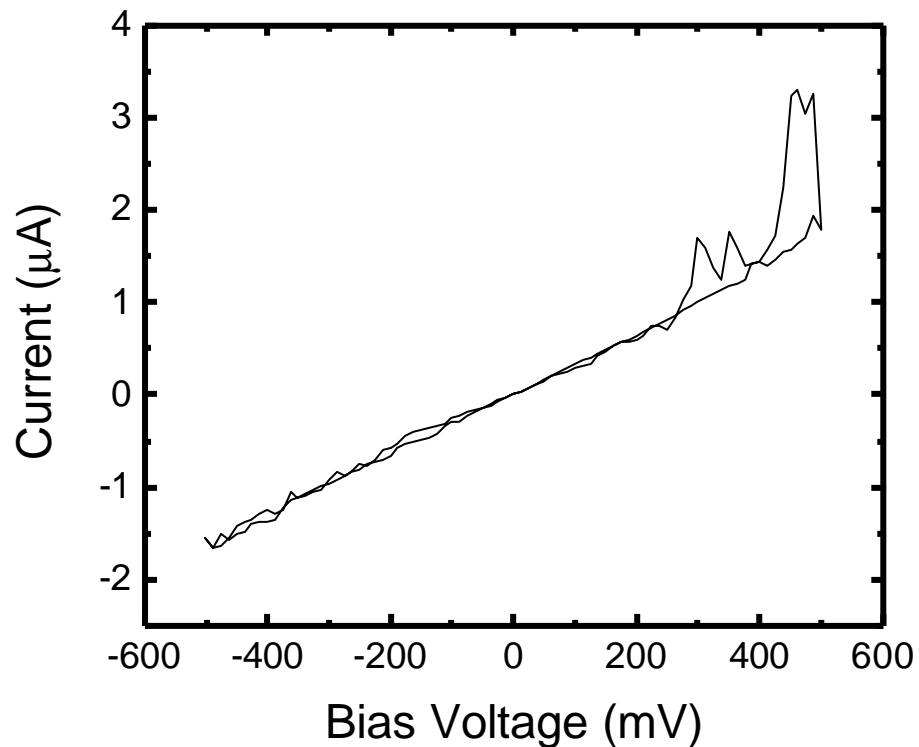


# Long Molecules: Device Fabrication

- Self assembly in solution



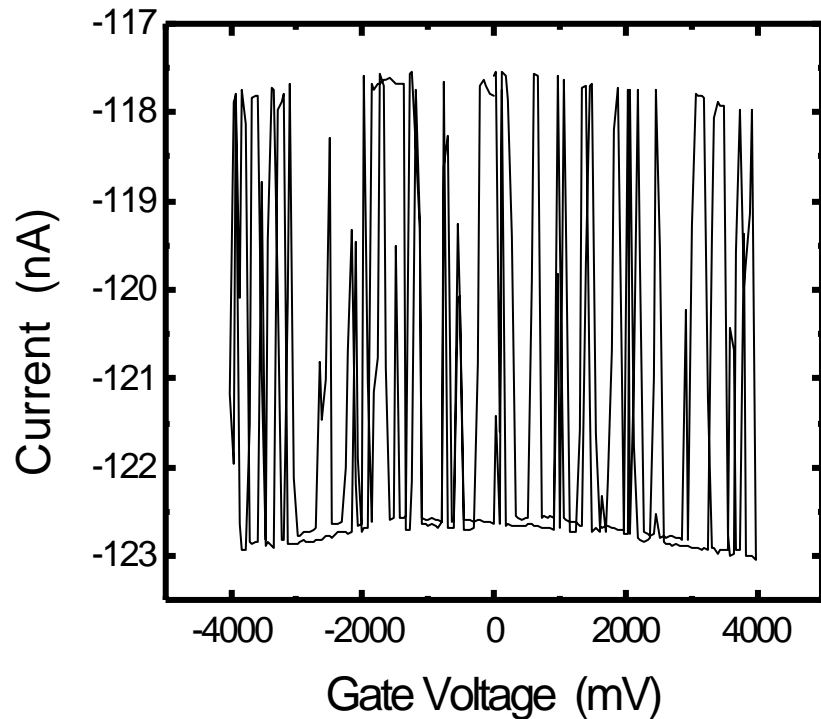
AG180 (~8nm)



# Long Molecules: Results

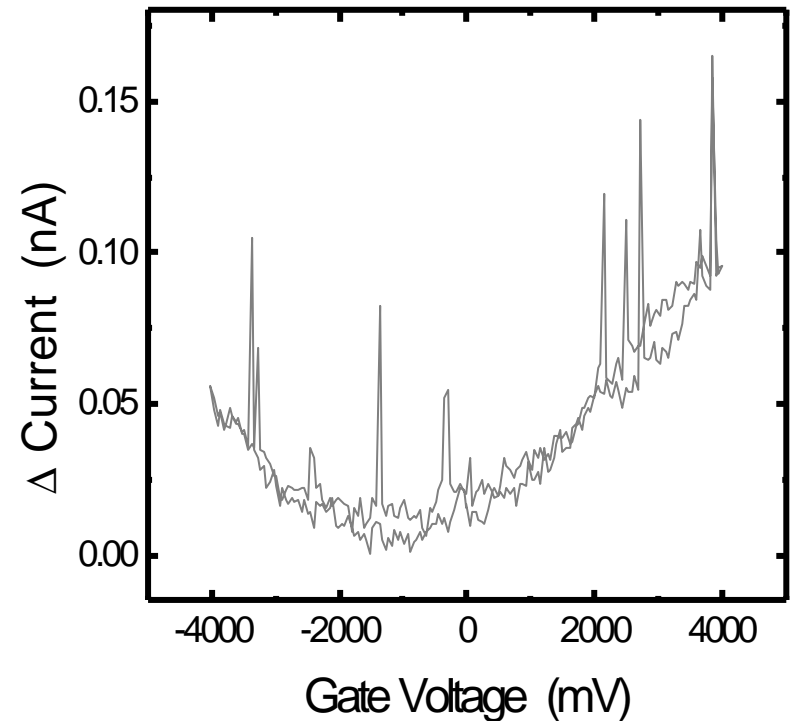
## Switching

Bias Voltage: -100 mV



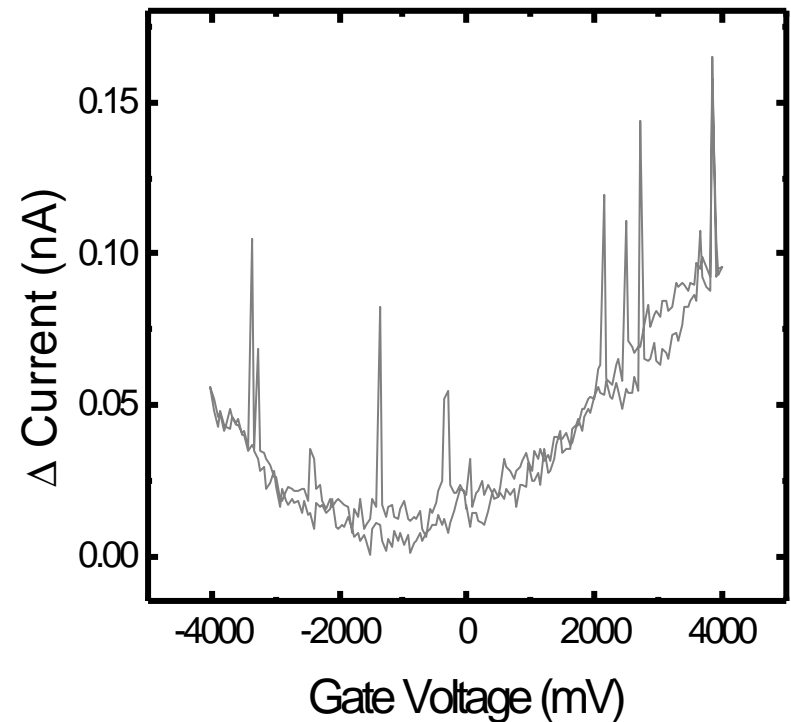
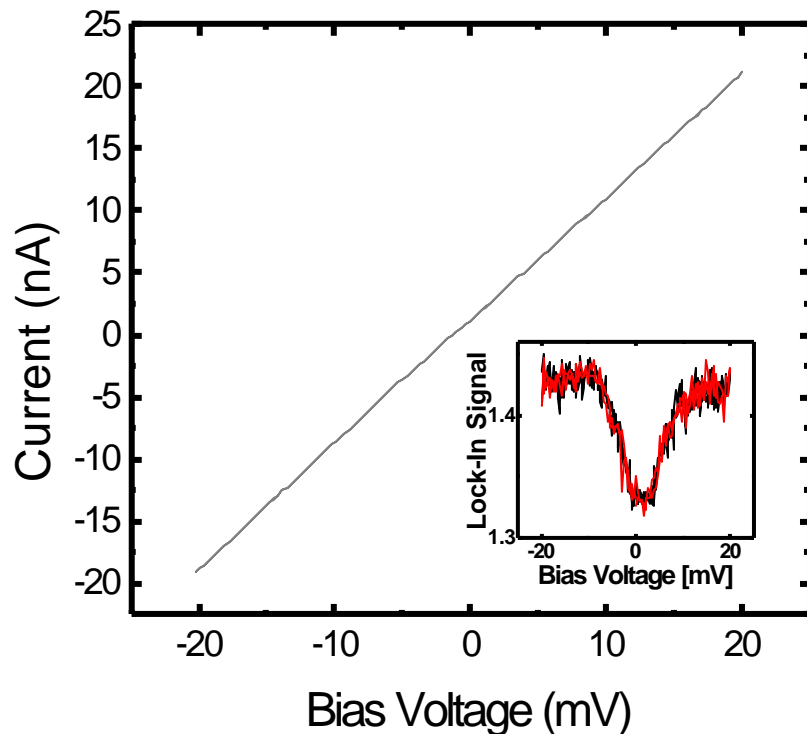
## Gate dependance

Bias Voltage: 20 mV



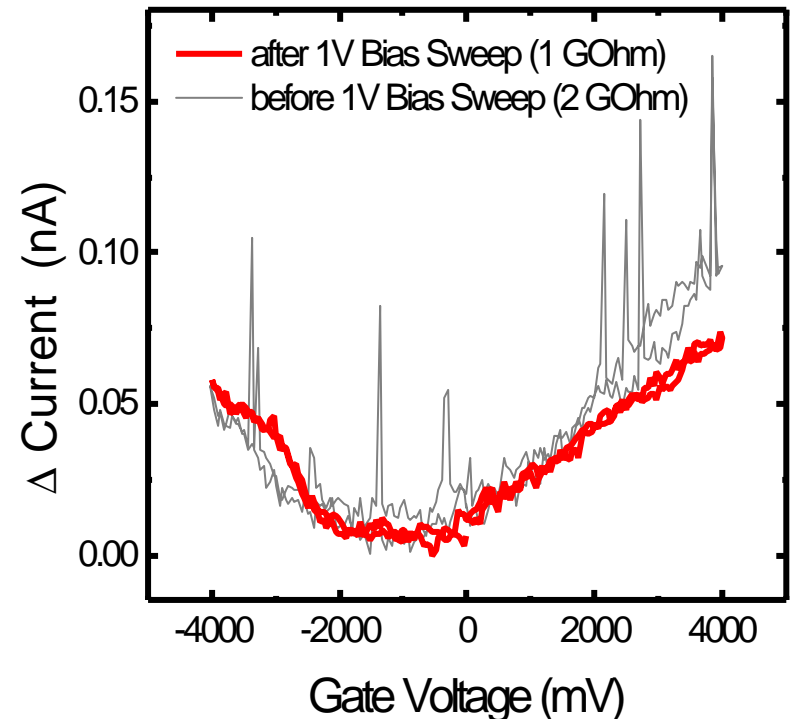
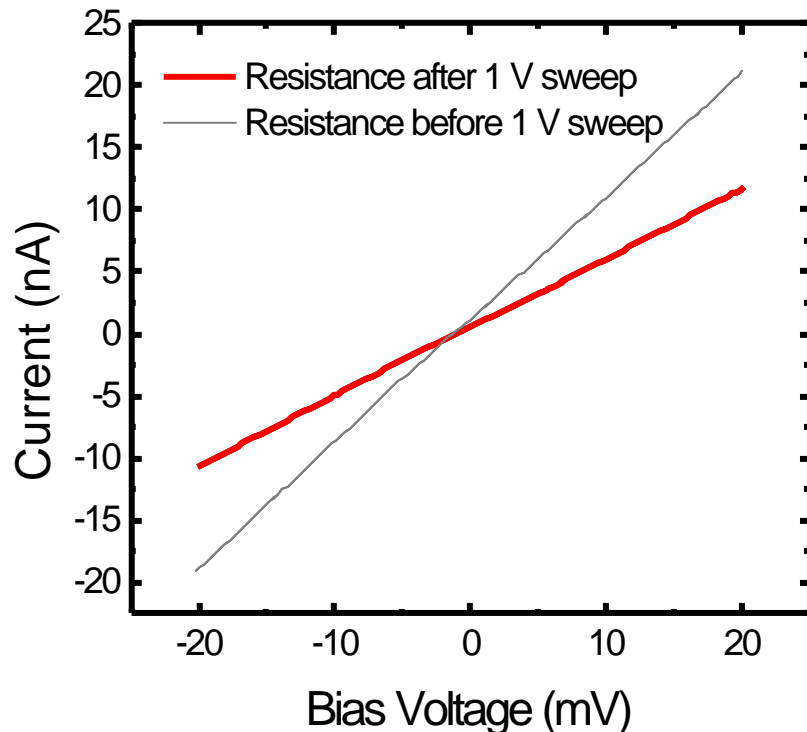
# Long Molecules: Results

- Gate dependance, conductance



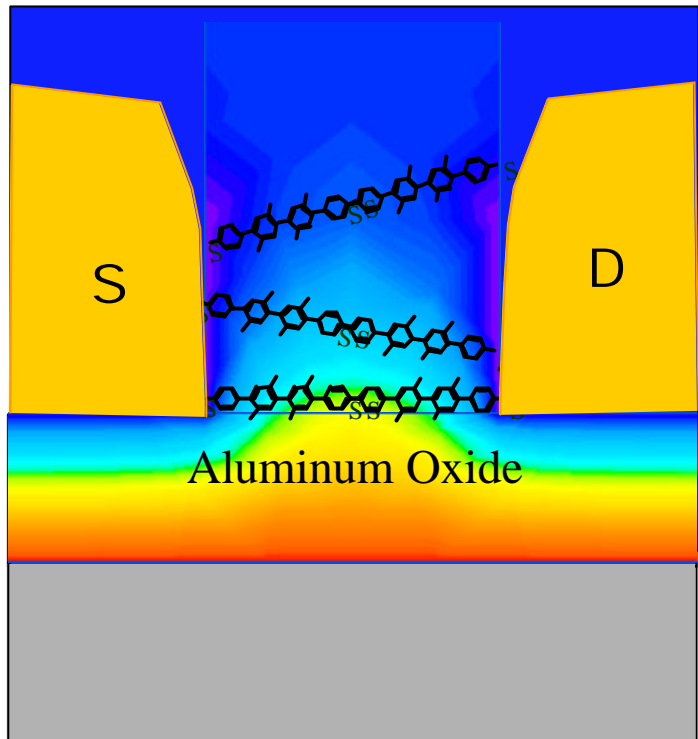
# Long Molecules: Results

- Gate dependance, conductance
- “Electrical annealing”



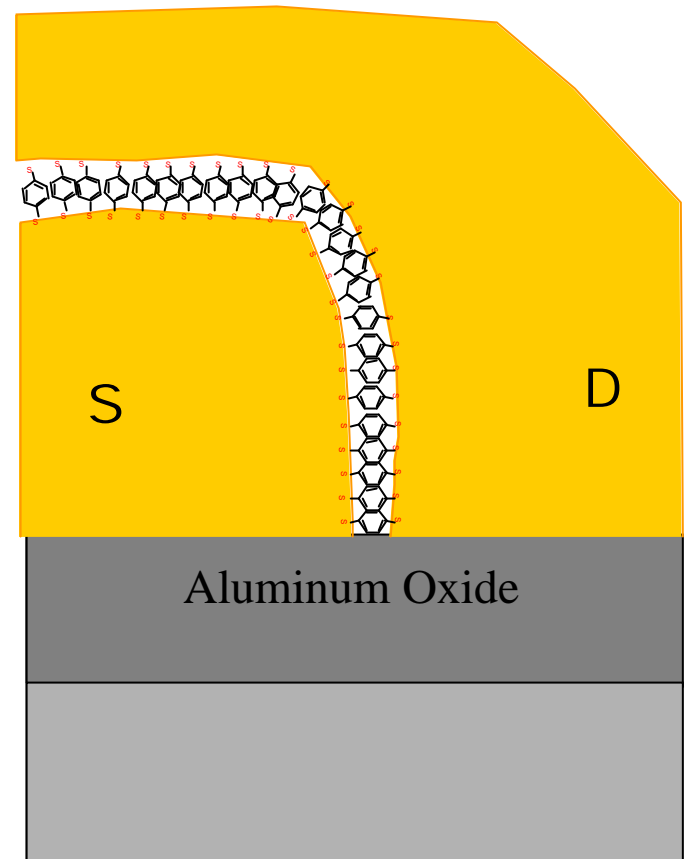
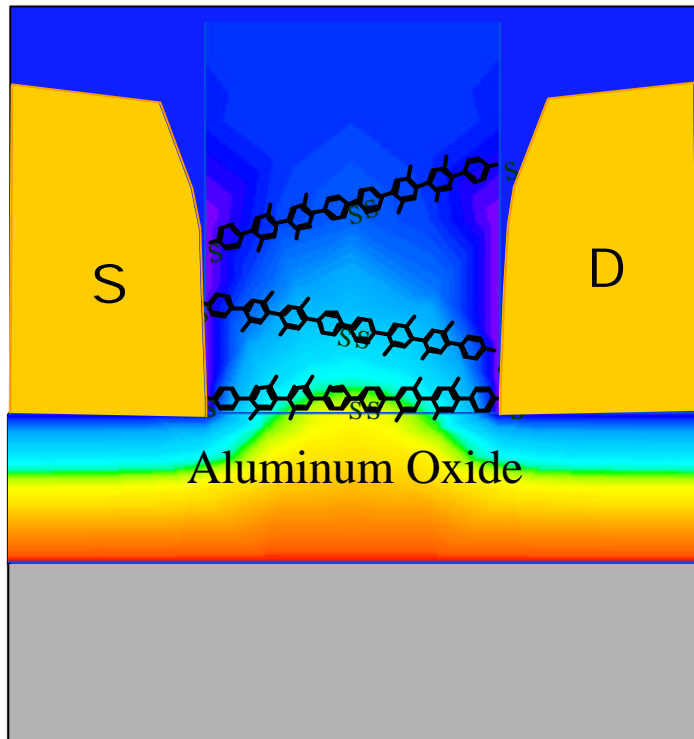
# Long and Short Molecules

- Expected gate effect



# Long and Short Molecules

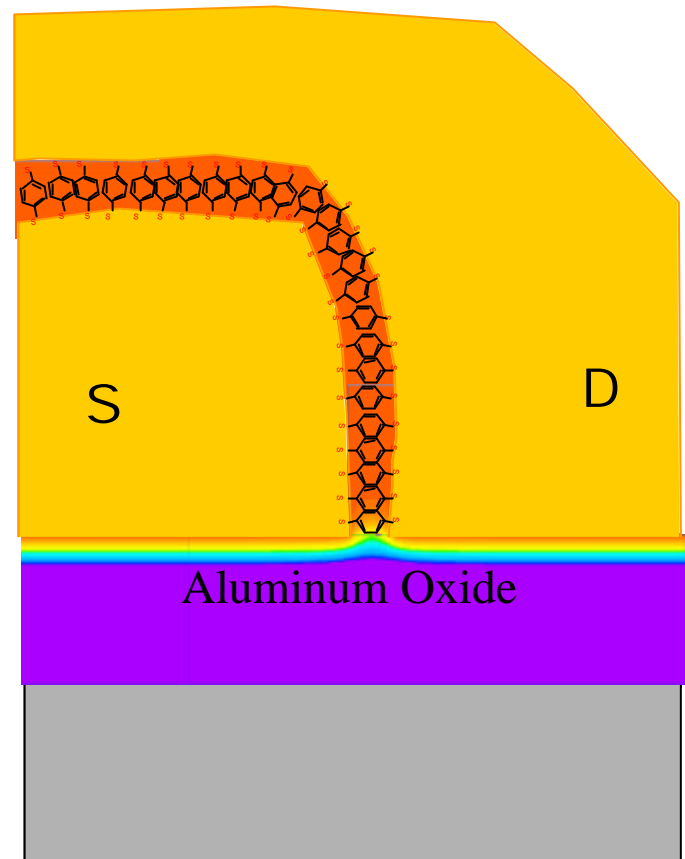
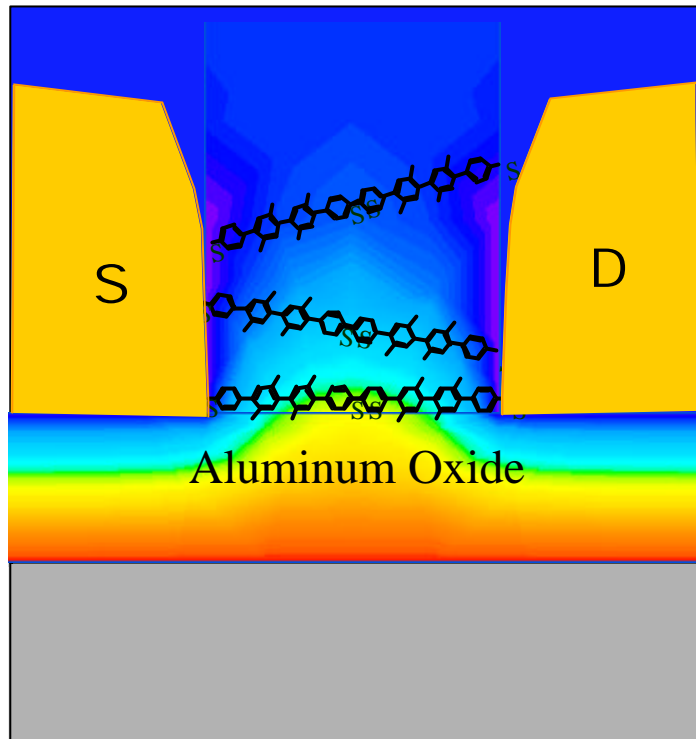
- Expected gate effect



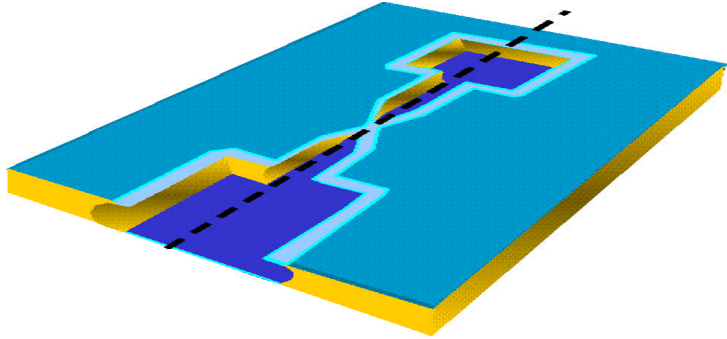


# Long and Short Molecules

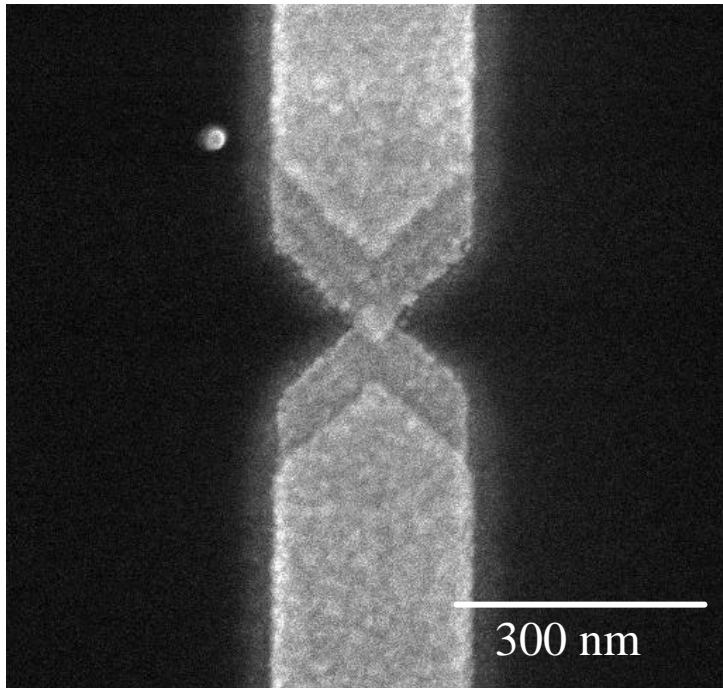
- Expected gate effect



# Short Molecules: Device Fabrication

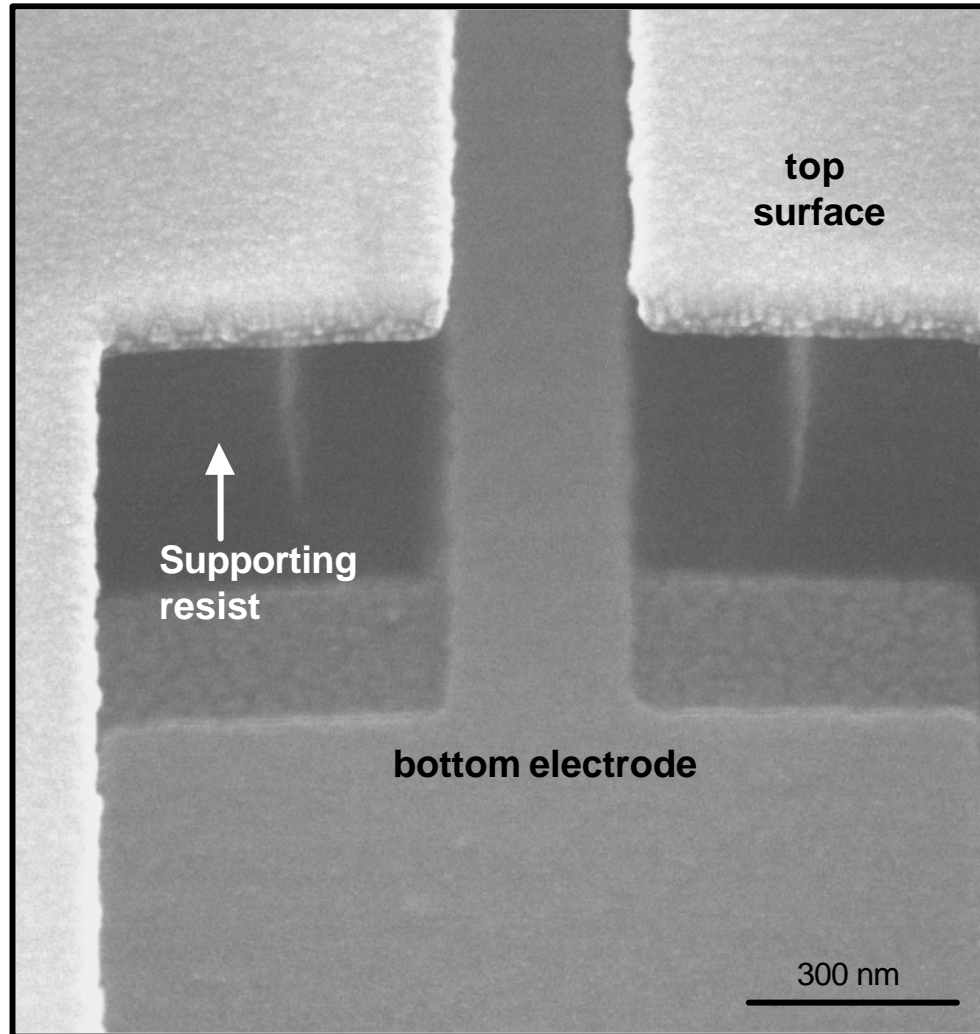
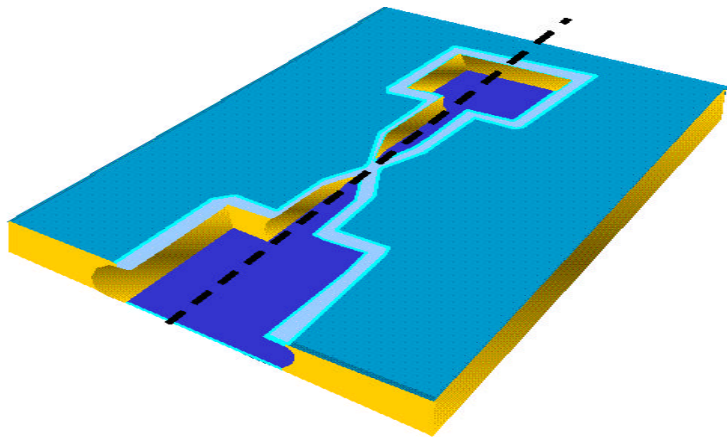


- Evaporation of first electrode
- **Formation of SAM**
- Evaporation of the second electrode
- Varying overlap sizes



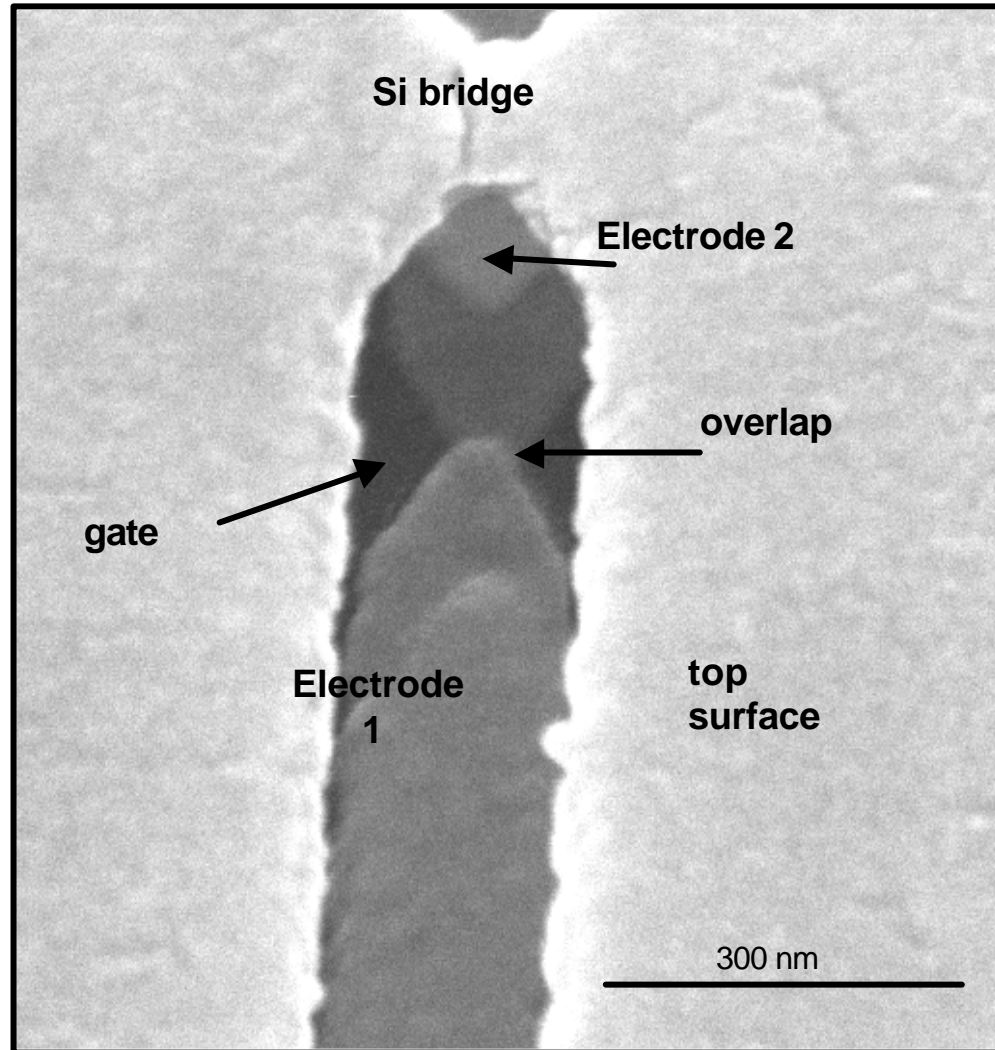
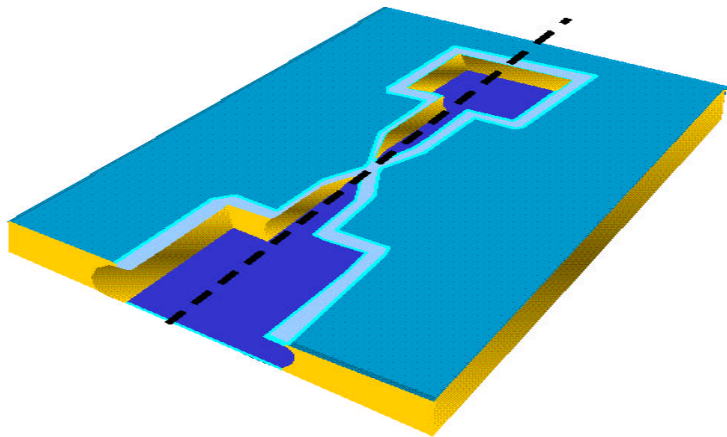
# Short Molecules: Device Fabrication

- New resist technique
  - PMMA
  - Si or SiN
  - Photoresist or SiO<sub>2</sub>
- SF<sub>6</sub> and O<sub>2</sub> etching
- No lift-off



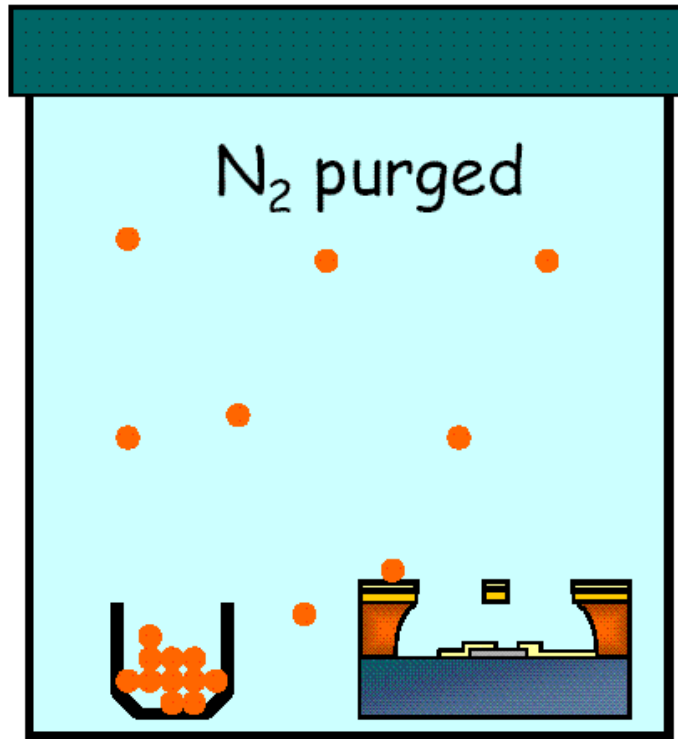
# Short Molecules: Device Fabrication

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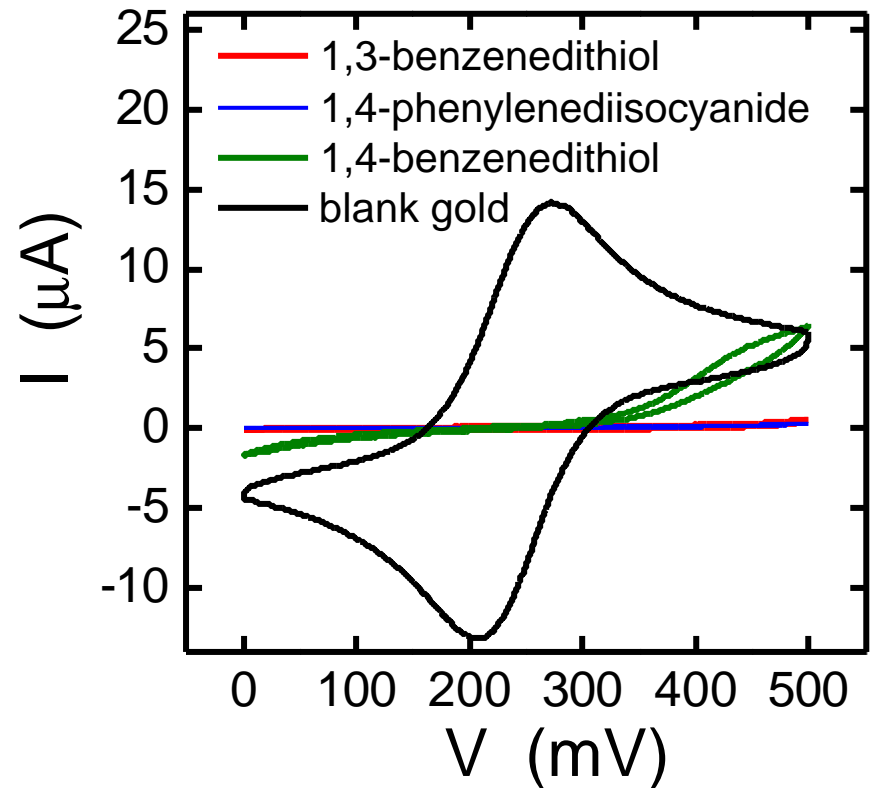


# Short Molecules: Device Fabrication

- Growth of SAM
  - Liquid
  - Gas

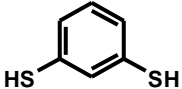
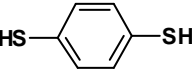

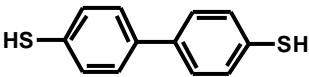
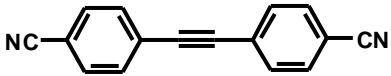


- Cyclic voltammetry
  - 1 mM K<sub>4</sub>[Fe(CN)<sub>6</sub>],  
0.5 M KCl



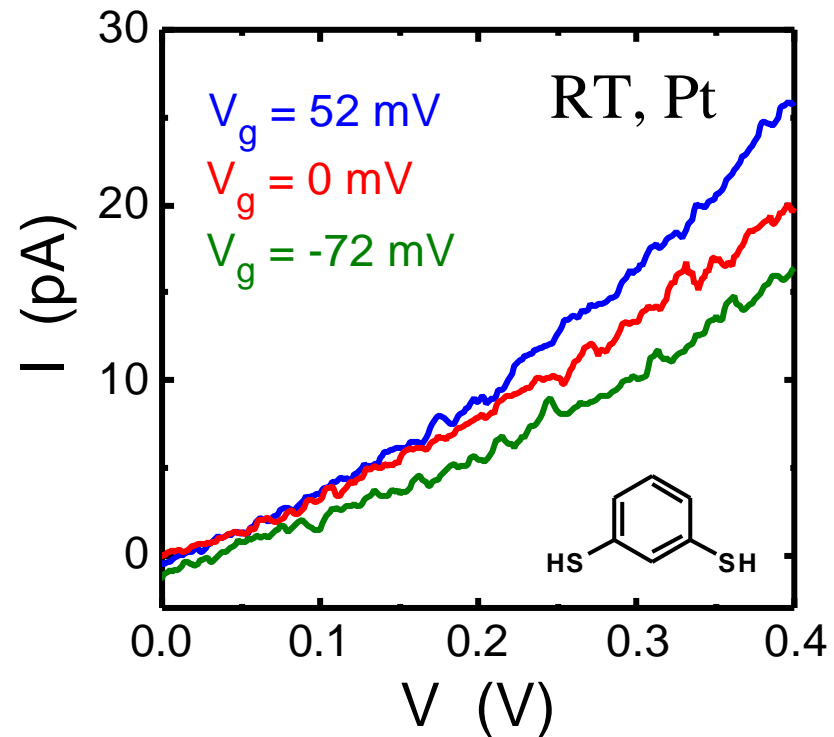
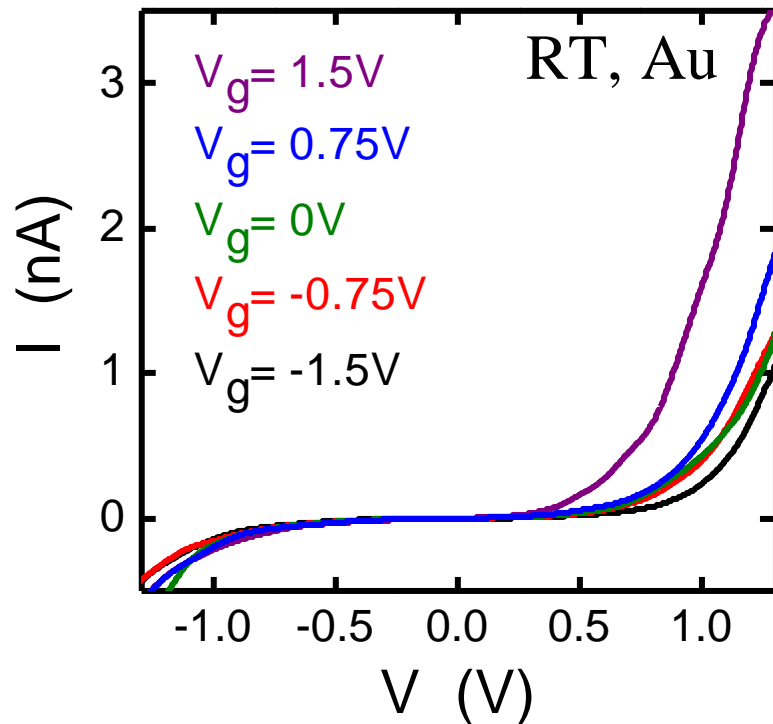
# Short Molecules: Device Fabrication

- Device yield

Molecules	Yield (%)	Total # of fabricated samples	Gate dependent samples	Liquid growth	Gas phase SAM growth	characteristics
1 	7.8	256	2	Y	Y	Asymmetric <i>I-V</i>
2 	0	216	0	Y	Y	
3 	16	236	0	Y	Y	NDC
4 	5	108	0	Y	N	NDC
5 	0	72	0	Y	N	

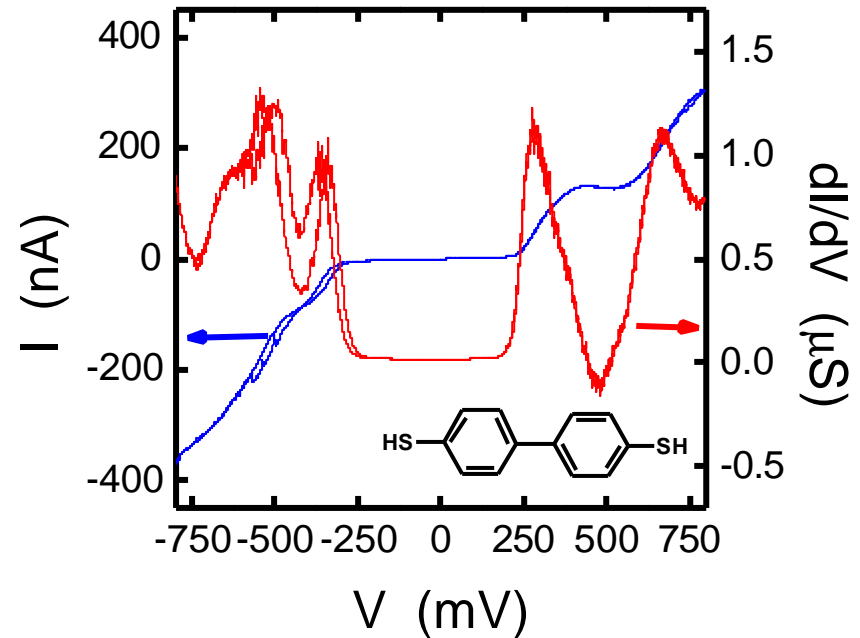
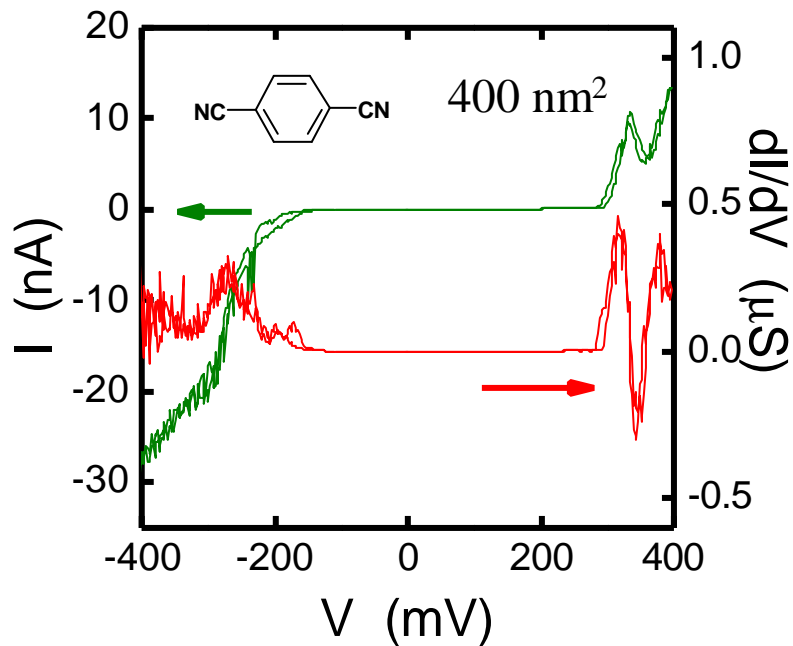
# Short Molecules: Results

- No gate effect
- Only two exceptions (out of 20) with 1,3 benzenedithiol
- Asymmetric IV curves



# Short Molecules: Results

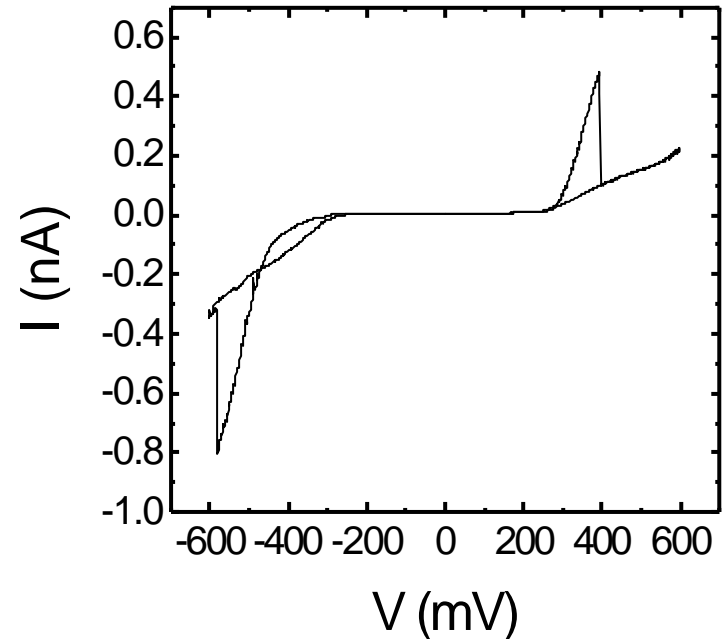
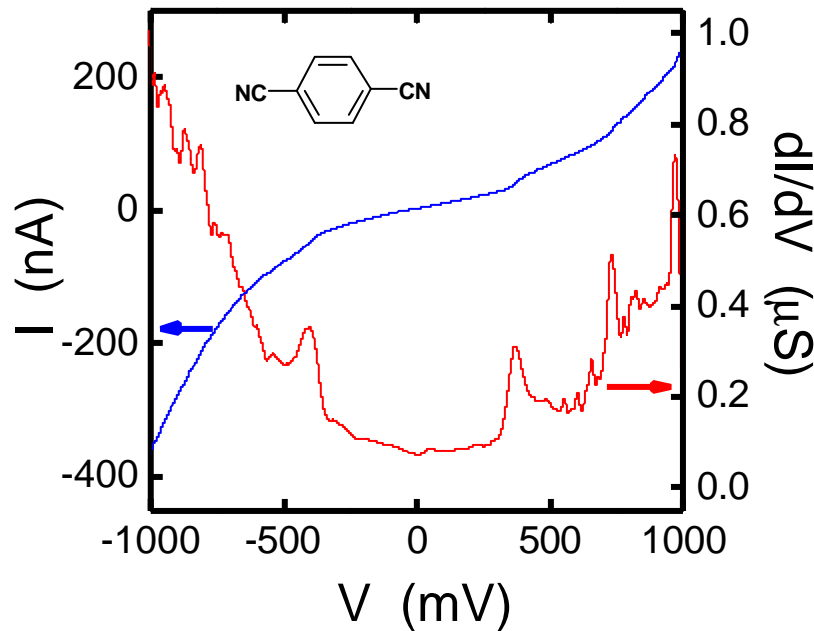
- Negative-differential resistance
  - 1,4-phenylenediisocyanide at 2 K for small overlap
  - 4,4'-biphenyldithiol





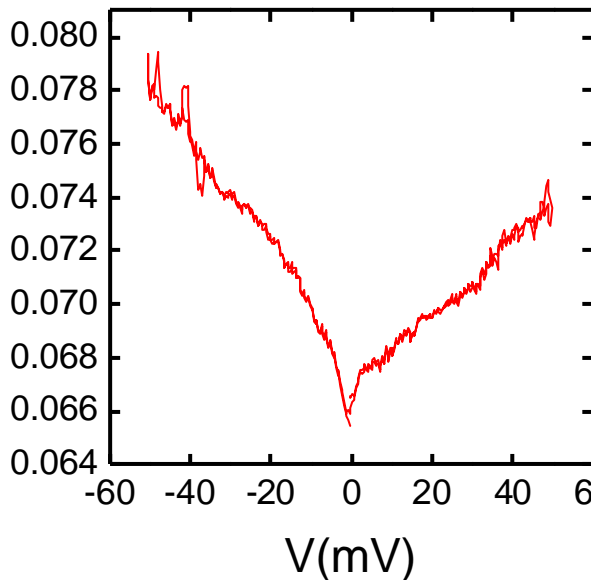
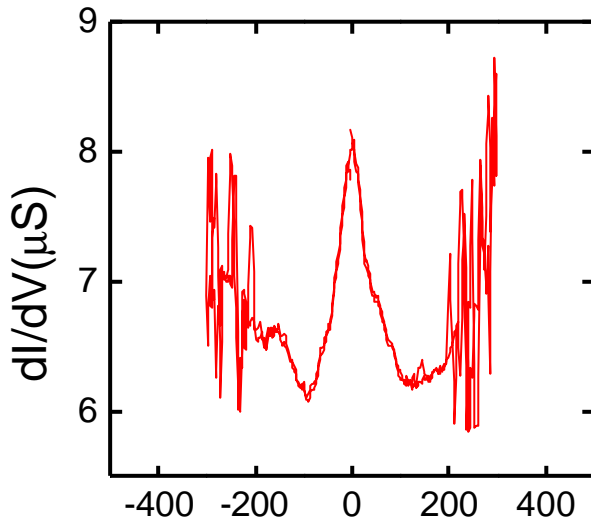
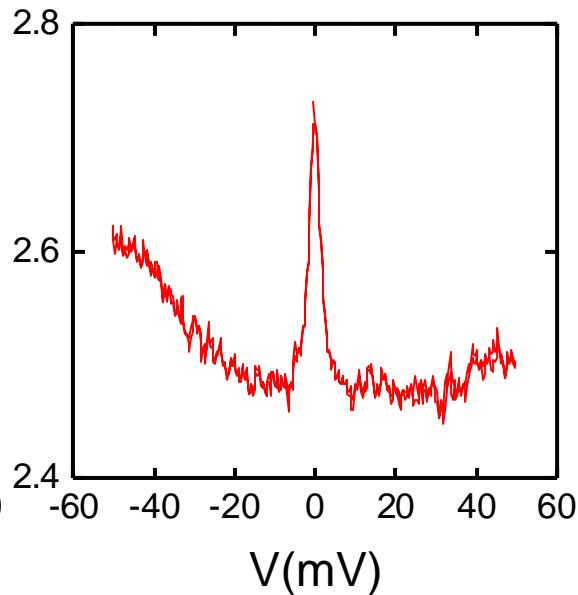
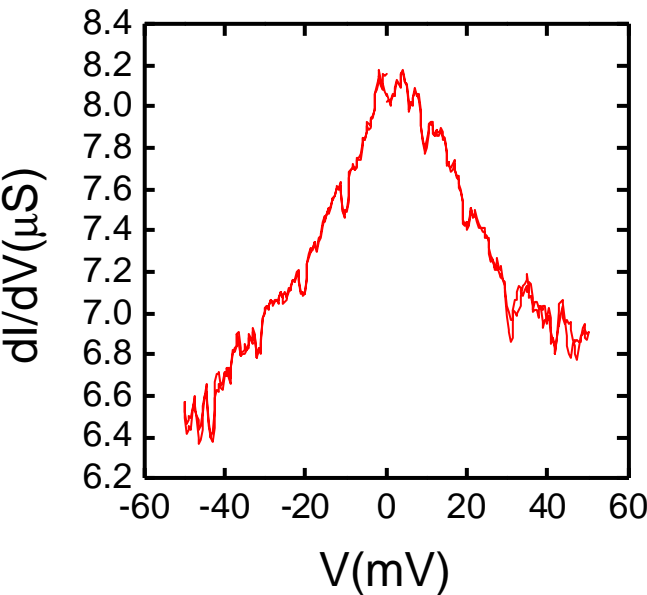
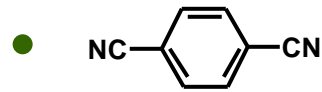
# Short Molecules: Results

- Switching with all molecules and overlap sizes
  - Switching behaviour for big overlap sample 1,4-phenylenediisocyanide at 4.2 K
  - Discrete even though many 1000s of molecules in parallel



# Short Molecules: Zero-Bias Peak

- Occasional anomalies in zero-bias conductance



# Conclusions

- Long molecules are more promising
  - Gate effect for long (8nm) molecules
  - No prospect for “SAMFET’s”
- Interesting nonlinear transport characteristics
  - NDR
- “Electrical annealing”